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| 1. Record Nr. | UNISALENTO991003443039707536 |
| Autore | Sciacca, Michele Federico |
| Titolo | L'uomo questo "squilibrato" : saggio sulla condizione umana / M. F. Sciacca |
| Pubbl/distr/stampa | [Roma] : Fratelli Bocca, stampa 1956 |
| Descrizione fisica | 331 p. ; 21 cm. |
| Collana | Opere complete di Michele Federico Sciacca ; 5 |
| Lingua di pubblicazione | Italiano |
| Formato | Materiale a stampa |
| Livello bibliografico | Monografia |
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- | | |
|-------------------------|---|
| 2. Record Nr. | UNINA9911004740003321 |
| Titolo | Electromigration in thin films and electronic devices : materials and reliability / / edited by Choong-Un Kim |
| Pubbl/distr/stampa | Oxford ; ; Philadelphia, : Woodhead Pub., c2011 |
| ISBN | 9780857093752
0857093754 |
| Edizione | [1st edition] |
| Descrizione fisica | 1 online resource (353 p.) |
| Collana | Woodhead Publishing Series in Electronic and Optical Materials |
| Altri autori (Persone) | KimChoong-Un |
| Disciplina | 621.38152 |
| Soggetti | Integrated circuits - Deterioration
Electrodiffusion
Thin films
Interconnects (Integrated circuit technology) |
| Lingua di pubblicazione | Inglese |
| Formato | Materiale a stampa |
| Livello bibliografico | Monografia |
| Note generali | Description based upon print version of record. |
| Nota di bibliografia | Includes bibliographical references and index. |
| Nota di contenuto | Part I. Introduction. Modeling electromigration phenomena / F. Cacho and X. Federspiel ; Modeling electromigratoin using the peridynamics approach / D.T. Read and V.K. Tewary and W.H. Gerstle ; Modeling, |

simulation and X-ray microbeam studies of electromigration / A.M. Maniatty, G.S. Cargill III, and H. Zhang -- Part II. Electromigration in copper interconnects. X-ray microbeam analysis of electromigration in copper interconnects / H. Zhang and G.S. Cargill III ; Voiding in copper interconnects during electromigration / C.L. Gan and M.K. Lim ; The evolution of microstructure in copper interconnects during electromigration / A.S. Budiman ; Scaling effects on electromigration reliability of copper interconnects / L. Zhang, J.W. Pyun, and P.S. Ho ; Electromigration failure in nanoscale copper interconnects / E.T. Ogawa -- Part III. Electromigration in solder. Electromigration-induced microstructural evolution in lead-free and lead-tin solders / K.-L. Lin ; Electromigration in flip-chip solder joints / D. Yang and Y.C. Chan and M. Pecht.

Sommario/riassunto

Understanding and limiting electromigration in thin films is essential to the continued development of advanced copper interconnects for integrated circuits. Electromigration in thin films and electronic devices provides an up-to-date review of key topics in this commercially important area. Part one consists of three introductory chapters, covering modelling of electromigration phenomena, modelling electromigration using the peridynamics approach and simulation and x-ray microbeam studies of electromigration. Part two deals with electromigration issues in copper interconnects, includin
